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The 145th Committee on Processing and Characterization of Crystals of the Japan Society for the Promotion of Science (JSPS)
Organizing Committee of the Forum on the Science and Technology of Silicon Materials 2014 (Hamamatsu)

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Preface

It is a great pleasure for us to welcome all of you to the 7th Forum on the Science and Technology of Silicon Materials (Silicon Forum) in Hamamatsu, Japan from October 19th to 22nd, 2014. This forum was founded by Professor Emeritus Koji Sumino (Tohoku University) in 1997 and 1999 at Kazusa Academia Park in Chiba Prefecture. Subsequently, the venues were changed to Shonan Village Center of Hayama-cho in Kanagawa Prefecture in 2001 and 2003, and to Toki Messe in Niigata Prefecture in 2007, and to Okayama University in 2010. The Okayama forum was co-organized by the 145th Committee on Processing and Characterization of Crystals of the Japan Society for the Promotion of Science (JSPS) together by the Organizing Committee of the Silicon Materials Science and Technology Forum.

The fundamental policy of the forum has been: (1) the promotion of the mutual cooperation between the people in the industry and the academia, (2) the education and stimulation of young scientists and engineers, and (3) the realization of face-to-face discussion on various issues concerning silicon materials at the international level. The forum has been playing an important role to transfer the fundamental knowledge to the new generations in the field of the science and technology of silicon materials. One should point out that this forum is one of a few international conferences, for which Japanese scientists and engineers have been organizing voluntarily. The scope of the forum has been extended from the original topics, i.e., growth technologies of bulk silicon and epi-wafers, characterization and control of defects and impurities, gettering and wafer technologies, to the topics on SIMOX, SOI, SGOI and strained wafer technologies, high-power devices, solar cells and photovoltaic materials.

The 7th forum has moved to Hamamatsu in Shizuoka prefecture. Hamamatsu area thrived along the old Tokaido, the main road which for centuries has connected Tokyo and Kyoto. Today there still stands many cultural properties showing this historical legacy. For instance, Hamamatsu Castle, built by Tokugawa Ieyasu, should not be missed. There are three major industries: motorcycles, musical instruments, and textiles. In recent years, however, high-tech industries like optics and electronics are achieving rapid development, which are closely related to this silicon forum.

On behalf of the organizing committee we would like to express our sincere thanks to Prof. Michio Tajima, general chairperson of the 145 committee for the Japan Society for the Promotion of Science, Institute Space and Astro. Sci. / JAXA & Meiji Univ., and Prof. Fumio Shimura, Shizuoka Institute of Science and Technology for many warm supports during the preparation for this forum.

October 19, 2014

Yutaka YOSHIDA, Shizuoka Institute of Science and Technology
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SP01, SP02, SP03, SP04, SP05, SP06, SP07, SP08, SP09, SP10, SP11, SP12, SP13, SP14, SP15, SP16, SP17, SP18, SP19, SP20
<table>
<thead>
<tr>
<th>Company Name</th>
<th>Page Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>TOKAIRIKI corporation</td>
<td>SP21</td>
</tr>
<tr>
<td>Vector Semiconductor Co., Ltd.</td>
<td>SP21</td>
</tr>
<tr>
<td>Toyo Tanso Co., Ltd.</td>
<td>SP22</td>
</tr>
<tr>
<td>Nihon Denkei co., ltd.</td>
<td>SP22</td>
</tr>
<tr>
<td>Shimadzu Corporation</td>
<td>SP23</td>
</tr>
<tr>
<td>Napson corporation</td>
<td>SP23</td>
</tr>
<tr>
<td>Hitachi High-Technologies Corporation</td>
<td>SP24</td>
</tr>
<tr>
<td>Philtech Inc.</td>
<td>SP24</td>
</tr>
<tr>
<td>KOBELCO Research Institute, Inc.</td>
<td>SP25</td>
</tr>
<tr>
<td>Shizuoka Institute of Science and Technology</td>
<td>SP26</td>
</tr>
</tbody>
</table>
Contents

(1) Session  Diffusion & Defects in Si materials

S1-1  Diffusion and point defects in silicon materials ....................................................... 1
       H. Bracht
       (Institute of Materials Physics, University Münster)

S1-2  Defect engineering in silicon materials ..................................................................... 2
       W. Bergholz
       (School of Engineering and Science, Jacobs University)

(2) Session  Defects & Impurities

S2-1  Atomic defects and impurities in silicon materials based on density functional theory ----------- 20
       J. Coutinho
       (Department of Physics and I3N, University of Aveiro)

S2-2  Defect evaluation techniques for electronic and solar grade silicon ............................... 22
       A.R. Peaker* and V.P. Markevich
       (Photon Science Institute, University of Manchester)

S2-3  The role of time scale in oxide precipitate nucleation during processing of Czochralski silicon material ......................................................................................................................... 33
       G. Kissinger1*, D. Kot1, and A. Sattler2
       (1IHP)
       (2Siltronic AG)

S2-4  Surface acoustic wave diagnosis of vacancy orbital in surface layer of silicon wafer .......... 46
       T. Goto1, K. Mitsumoto1, M. Akatsu1, S. Baba1, K. Okabe1,2, R. Takasu1, Y. Nemoto1,
       (1Graduate School of Science and Technology, Niigata University)
       (2GlobalWafers Japan Co., Ltd.)
       (3Department of Electrical Engineering and Electronics, Kyushu Institute of Technology)
       (4Philtech Inc.)
       (5Toshiba Corporation)
(3) Session  
**Power devices and related materials**

**S3-1** Silicon power device and the material requirements  
-For new generation power electronics-  
  I. Omura  
  (Kyushu Institute of Technology)

**S3-2** Defects and impurities in Si wafers for power devices  
H. Yamamoto  
(Department of Electrical, Electronics and Computer Engineering, Chiba Institute of Technology)

**S3-3** Nondestructive imaging and discrimination of extended defects in 4H-SiC  
H. Tsuchida*, R. Tanuma, M. Nagano, I. Kamata, and T. Miyazawa  
(Central Research Institute of Electric Power Industry (CRIEPI))

**S3-4** Top-seeded solution growth of SiC single crystal using metal solvents  
K. Kusunoki, K. Kamei, K. Seki, N. Okada, Y. Kishida, K. Moriguchi, and H. Kaidoh  
(Advanced Technology Research Laboratories, Nippon Steel & Sumitomo Metal Corporation)

(4) Session  
**Short presentations**

**S04-1** Poster presentations

**PT01-1** Strain-enhanced diffusion originated from end-of-range defects  
T. Isoda*, M. Uematsu, and K.M. Itoh  
(School of Fundamental Science and Technology, Keio University)

**PT01-2** Effect of dynamics on the elastic softening of vacancy in Si  
K. Shirai and J. Ishisada  
(The Institute of Science and Industrial Research, Osaka University)

**PT01-3** Sb-doping effect on the dislocation motion in various Si1-xGex films  
S. Maki1*, Y. Yamashita1, T. Fushimi1, Y. Ohno2, I. Yonenaga2, T. Nishikawa1, and Y. Hayashi1  
(1Graduate School of Natural Science and Technology, Okayama University)  
(2Institute for Materials Research, Tohoku University)

**PT01-4** Influence of RTA pre-treatment on the Morphology of oxygen precipitates in Czochralski silicon wafers observed by FTIR spectroscopy and STEM  
D. Kot1*, G. Kissinger1, M.A. Schubert1, and A. Sattler2  
(1IHP)  
(2Siltronic AG)
PT01-5  Effect of surface-nitrogen-concentration on dislocation behavior in Si wafers treated by high temperature rapid thermal nitridation  
S. Chokyu¹, S. Takeuchi²*, H. Asazu², Y. Nakamura², H. Sudo³, K. Araki³, K. Izunome³, and A. Sakai²  
¹School of Engineering Science, Osaka University  
²Graduate School of Engineering Science, Osaka University  
³Base Technology, Technology, GlobalWafers Japan Co., Ltd.

PT01-6  Self-diffusion in silicon under proton irradiation  
T. Südkamp¹*, J. K. Prüßing¹, J. N. Klug², V.V. Voronkov³, R. Falster³, and H. Bracht¹  
¹Institute of Materials Physics, University of Münster  
²rubitec Bochum GmbH  
³MEMC Electronic Materials

PT02-1  Effect of doping on silicon nanowire over rectangular crosssection  
A. Chatterjee  
(Materials Science, Accelrys K.K.)

PT02-2  Search for FeB pairs in highly B-doped Si wafers by Mössbauer spectroscopy  
K. Tanaka¹*, T. Watanabe², T. Uenoyama², Y. Ino¹, and Y. Yoshida²  
¹Center for Advanced Technology, Shizuoka Institute of Science and Technology (SIST)  
²Faculty of Science and Technology, SIST

PT02-3  First-principles calculation of single copper impurity in silicon  
T. Fujimura and K. Shirai  
(Nanoscience and Nanotechnology Center, The Institute of Scientific and Industrial Research, Osaka University)

PT03-1  Thermoelectric characteristics of Si- and Ge-on-insulator layers for predicting those of SiGe nanostructures  
V. Manimuthu¹,², S. Yoshida¹, Y. Suzuki¹, F. Salleh¹, M. Arivanandhan¹, Y. Kamakura³, Y. Hayakawa¹,² and H. Ikeda¹,²  
¹Research Institute of Electronics, Shizuoka University  
²Graduate School of Science and Technology, Shizuoka University  
³Graduate School of Engineering, Osaka University
PT04-1  Effects of position of mirror-lamp system on silicon crystal growth by mirror-shifting-type infrared convergent-heating floating zone method ......................................................... 122
    Md.M. Hossain1*, S. Watauchi1,2, M. Nagao1, and I. Tanaka1
    (1Center for Crystal Science and Technology, University of Yamanashi)
    (2Precursory Research for Embryonic Science and Technology (PRESTO), Japan Science and
    Technology Agency (JST))

PT04-2  Constitutional supercooling in Czochralski Si crystal growth heavily doped
    with B, Ge and As ........................................................................................................ 126
    T. Taishi1*, I. Yonenaga2, and K. Hoshikawa1
    (1Faculty of Engineering, Shinshu University)
    (2Institute for Materials Research, Tohoku University)

PT04-3  Numerical investigation of carbon and silicon carbide contamination
    during the melting process of Czochralski silicon crystal growth.............................. 131
    X. Liu*, B. Gao, S. Nakano, and K. Kakimoto
    (Research Institute for Applied Mechanics, Kyushu University)

PT05-1  Effective gettering sites for metal impurities in Si wafers searched
    by first principles calculation ......................................................................................... 134
    S. Shirasawa*, and K. Sueoka
    (Department of Communication Engineering, Okayama Prefectural University)

PT05-2  Ab initio analysis on stability of metal atoms in β-Si3N4/Si structure ....................... 140
    D. Shibata*, S. Kobayashi, and K. Sueoka
    (Department of Communication Engineering, Okayama Prefectural University)

PT06-1  Development of Mössbauer spectroscopic microscope to evaluate Si solar cells .... 149
    Y. Ino1*, H. Soejima1, K. Hayakawa1, K. Yukihiro1, K. Tanaka1, H. Fujita1, T. Watanabe1,
    Y. Harada2, and Y. Yoshida1
    (1Shizuoka Institute of Science and Technology)
    (2APCO. Ltd.)
PT07-1  Ge-rich SiGe waveguide for integration of Ge/SiGe quantum wells
electro-absorption components on bulk silicon substrate ................................. 157
P. Chaisakul1,2*, D.M.-Morini2, J. Frigerio3, V. Vakarin2, S. Cecchi3, D. Chrastina3, K. Wada1,
G. Isella3, and L. Vivien2
(1Department of Materials Engineering, The University of Tokyo)
(2Institut d'Electronique Fondamentale, Université Paris-Sud)
(3L-NESS, Dipartimento di Fisica del Politecnico di Milano)

PT07-2  Traveling plasmon interaction with light ......................................................... 165
Y. Deng*, Y. Mizushima, and K. Wada
(Department of Materials Engineering, The University of Tokyo)

PT07-3  Effect of excitation light intensity on micro-photoluminescence spectra for Ge:
a comparison with Si, GaAs and InGaAs ................................................................ 172
N. Higashitarumizu, and Y. Ishikawa*
(Department of Materials Engineering, The University of Tokyo)

PT09-1  Reduction of dislocation density by cooling optimization in Si crystal growth ...... 176
K. Jiptner1*, H. Harada1, Y. Miyamura1, B. Gao2, M. Fukuzawa3, K. Kakimoto2,
and T. Sekiguchi1
(1Nano-Device Characterization Group, National Institute for Materials Science)
(2Research Institute for Applied Mechanics, Kyushu University)
(3Graduate School of Science and Technology, Kyoto Institute of Technology)

PT09-2  50 cm square sized seed cast mono Si ingot growth ........................................ 182
Y. Miyamura1,2, H. Harada1, T. Sekiguchi1,2*, S. Nakano3, and K. Kakimoto3
(1National Institute for Materials Science)
(2MANA Nanoelectronic Materials Unit, Graduate School of Pure and Applied Sciences,
University of Tsukuba)
(3Research Institute for Applied Mechanics, Kyushu University)

PT09-3  First principles analysis of atomic configurations of group IV elements
in Ge crystal for solar cells ...................................................................................... 186
R. Matsutani*, K. Sueoka, and E. Kamiyama
(Department of Communication Engineering, Okayama Prefectural University)
PT09-4  Bansic study on energy band structures of group IV compound semiconductors for solar cells
R. Suwa*, K. Sueoka, and E. Kamiyama
(Department of Communication Engineering, Okayama Prefectural University)

PT09-5  Numerical analysis of the relationship between the crystal growth method and dislocation density in multicrystalline silicon for solar cells
S. Nakano, B. Gao, and K. Kakimoto
(Research Institute for Applied Mechanics, Kyushu University)

PT09-6  Calculation of temperature distribution for controlling growth of dendrite crystals to decrease dislocation density in a multicrystalline Silicon ingot
T. Hiramatsu*, I. Takahashi, S. Matsushima, and N. Usami
(Department of engineering, Nagoya University)

PT09-7  Electric-field effects on the stability of impurity levels on a grain boundary in mc-Si for solar cells
M. Yabuki*, Y. Yamashita, T. Tokura, T. Nishikawa, and Y. Hayashi
(Graduate School of Natural Science and Technology, Okayama University)

PT09-8  Extended defects in multicrystalline Silicon grown by directional solidification using polycrystalline template
R.R. Prakash¹,²*, K. Jiptner¹, J. Chen¹, Y. Miyamura¹, H. Harada¹, and T. Sekiguchi¹,²
(¹MANA Nanoelectronic Materials Unit, National Institute for Materials Science)
(²Doctoral Program for Pure and Applied Sciences, University of Tsukuba)

PT10-1  Practical thermal condition of silicon CVD reactor for minimal manufacturing
N. Li¹*, H. Habuka¹, S. Ikeda²,³, Y. Ishida²,³, and S. Hara²,³
(¹Yokohama National University)
(²National Institutes of Advanced Science and Technology)
(³Minimal Fab Development Association)

(5)Session  Si Crystal Growth
S5-1  Control of intrinsic point defects in single crystal silicon and germanium growth from a melt
J. Vanhellemont¹*, E. Kamiyama², K. Nakamura², and K. Sueoka²
(¹Department of Solid State Sciences, Ghent University)
(²Department of Communication Engineering, Okayama Prefectural University)
S5-2  Control of point defects in growing single crystal Si ................................................................. 236
    K. Nakamura
    (Okayama Prefectural University)

S5-3  Defect formation behavior due to interaction between hydrogen and point defects
    in CZ-Si crystal growth .................................................................................................................... 247
    W. Sugimura1,3*, T. Ono1, K. Nakamura2, M. Hourai1, and K. Higashida3
    (1Department of Advanced Evaluation & Technology Development, SUMCO CORPORATION)
    (2Department of Communication Engineering, Okayama Prefectural University)
    (3Department of Materials and Engineering, Kyushu University)

(6)Session  Si Wafer and Devices
S6-1  Current status and issues in development of 450mmm wafer ....................................................... 255
    K. Takaishi1*, T. Yoshino2, and Y. Yamada2
    (1SUMCO CORPORATION, Technology Division)
    (2SUMCO CORPORATION, Wafer Engineering & Development Section)

S6-2  Impact of rapid thermal oxidation at ultrahigh-temperatures on oxygen precipitation behavior in
    Czochralski-silicon crystals ............................................................................................................. 262
    (Base Technology, Technology, GlobalWafers Japan Co., Ltd.)

S6-3  Point defect control in Si crystal growth and wafer annealing ..................................................... 269
    R. Falster
    (MEMC Electronic Materials)

(7)Session  Evaluation techniques
S7-1  Quantitative analysis of donor and acceptor impurities in photovoltaic Si
    by photoluminescence spectroscopy ............................................................................................ 270
    M. Tajima1,2*, K. Tanaka1,2, K. Nakagawa1,2, H. Toyota1, and A. Ogura2
    (1Institute of Space and Astronautical Science / JAXA)
    (2Meiji University)

S7-2  Nuclear methods to study defects and impurities in Si materials
    using heavy ion accelerators ........................................................................................................... 278
    G. Langouche1 and Y. Yoshida2
    (1University of Leuven (KU Leuven))
    (2Shizuoka Institute of Science and Technology)
S7-3 Silicon quantum information processing
-----------------------------------------------
K.M. Itoh
(Department of Applied Physics, Keio University)

(8) Session  Photonics

S8-1 High-speed Si optoelectronic devices
-----------------------------------------------
L. Vivien¹*, L. Virot¹,²,³, J.M. Hartmann², J. M. Fédéli², D.M.-Morini¹, E. Cassan¹, C. Baudot¹, and F. Bœuf³
(¹Institut d’Electronique Fondamentale (IEF), Université Paris-Sud)
(²CEA, LETI)
(³STMicroelectronics)

S8-2 Optoelectronic devices based on Si, silica and Ge
-----------------------------------------------
H. Fukuda¹*, T. Tsuchizawa²,³, H. Nishi²,³, R. Kou²,³, T. Hiraki²,³, K. Takeda²,³, M. Usui¹, K. Okazaki²,³, K. Yamada²,³, T. Yamamoto², K. Honda², M. Nogawa¹, H.-J. Song², Y. Ishikawa⁴, K. Wada⁴, and T. Saida¹
(¹NTT Device Innovation Center, NTT Corp.)
(²NTT Device Technology Laboratories, NTT Corp.)
(³NTT Nanophotonics Center, NTT Corp.)
(⁴Graduate School of Material Engineering, The University of Tokyo)

S8-3 Monolithic integrated Ge light emitters
-----------------------------------------------
K. Oda¹*, K. Tani¹, T. Okumura¹, Y. Suwa¹, and T. Ido¹
(¹Photonics Electronics Technology Research Association (PETRA))
(²Institute for Photonics-Electronics Convergence System Technology (PECST))
(³Central Research Laboratory, Hitachi Ltd.)

(9) Session  Recent topics from Hamamatsu

S9-1 The development of CCD image sensor for Subaru telescope by Hamamatsu
-----------------------------------------------
H. Suzuki*, M. Muramatsu, Y. Miyazaki, and S. Takagi
(Solid State Division, Hamamatsu Photonics K.K.)

S9-2 Silicon detectors for ATLAS and CMS experiments at LHC
-----------------------------------------------
K. Yamamura* and Y. Ishikawa
(Solid-State Division, Hamamatsu Photonics K.K.)
(10) Session  

**Solar cells/crystal growth**

**S10-1**  
Computer simulation of crystal growth for Si solar cells  
K. Kakimoto and B. Gao  
(Research Institute for Applied Mechanics, Kyushu University)

**S10-2**  
Large-scale implementation of floating cast method to grow high-quality multicrystalline silicon ingot for solar cells  
N. Usami, I. Takahashi, S. Joonwichien, T. Hiramatsu, and S. Matsushima  
(Graduate School of Engineering, Nagoya University)

**S10-3**  
Gettering and hydrogenation of interstitial iron in silicon for solar cells  
D. Macdonald*, A.Y. Liu, and S.P. Phang  
(Research School of Engineering, The Australian National University)

**S10-4**  
The impact of Ge codoping on grown-in microdefects and photovoltaic characteristics of B-doped Czochralski grown Si crystal  
M. Arivanandhan¹*, R. Gotoh², K. Fujiwara², S. Uda², Y. Hayakawa¹, and M. Konagai³  
(¹Research Institute of Electronics, Shizuoka University)  
(²Institute for Materials Research, Tohoku University)  
(³Department of Physical Electronics, Tokyo Institute of Technology)

(11) Session  

**Si technology for future**

**S11-1**  
Technology trends and business challenges in silicon wafer industry  
S. Kohyama  
(GlobalWafers Japan Co., Ltd.)
<table>
<thead>
<tr>
<th>#</th>
<th>Time</th>
<th>Session Subjects</th>
<th>Title</th>
<th>Name</th>
<th>Affiliation</th>
<th>Nationality</th>
</tr>
</thead>
<tbody>
<tr>
<td>S1-1</td>
<td>15:30-15:40</td>
<td>Opening</td>
<td>(1) Session Diffusion &amp; Defects in Si materials</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S1-2</td>
<td>15:40-16:40</td>
<td>Poster session</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S1-3</td>
<td>16:40-17:40</td>
<td>Get-together party</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-2</td>
<td>17:40-18:40</td>
<td>Lunch</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-3</td>
<td>18:40-19:40</td>
<td>Banquet</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-4</td>
<td>13:30-14:30</td>
<td>Defects &amp; Impurities</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-5</td>
<td>14:30-15:30</td>
<td>Silicon Power Device and the Material Requirements</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-6</td>
<td>15:30-16:30</td>
<td>Present status and problems in development of 450 mm wafer</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-7</td>
<td>16:30-17:30</td>
<td>Point defect control in Si crystal growth and wafer annealing</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-8</td>
<td>17:30-18:30</td>
<td>Evaluation techniques</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-9</td>
<td>18:30-19:30</td>
<td>Recent topics from Hamamatsu</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>S2-10</td>
<td>19:30-20:30</td>
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<td>S2-11</td>
<td>20:30-21:30</td>
<td>Excursion</td>
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**Sunday 19th October**

- **Opening**: 15:30-15:40
- **Poster session**: 15:40-16:40
- **Get-together party**: 16:40-17:40
- **Coffee/Lunch**: 17:40-18:40
- **Banquet**: 18:40-19:40

**Monday 20th October**

- **Session subjects**: 13:20-14:30
- **Coffee**: 14:30-15:00
- **Lunch**: 15:00-15:20
- **Coffee**: 15:20-16:00
- **Lunch**: 16:20-16:40
- **Coffee**: 16:40-17:00
- **Banquet**: 17:00-18:00

**Tuesday 21st October**

- **Si Crystal Growth**
- **Evaluation techniques**
- **Recent topics from Hamamatsu**
- **Solar cells / crystal growth**

**Wednesday 22nd October**

- **Closing**
- **Excursion**